Shantou Huashan Electronic Devices Co.,Ltd.

NPN SILICON TRANSISTOR

HX2785

APPLICATIONS

Amplifier And Speed Switching.

ABSOLUTE MAXIMUM RATINGS (T_a=25℃)

T_{stg}——Storage Temperature····· -55~150℃

T_j——Junction Temperature·····150℃

P_C——Collector Dissipation·····250mW

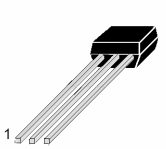
V_{CBO}——Collector-Base Voltage·····60V

V_{CEO}——Collector-Emitter Voltage·····50V

V_{EBO}——Emitter-Base Voltage·····5V

I_C——Collector Current·····100mA

TO-92S



1—Emitter，E
2—Collector，C
3—Base，B

ELECTRICAL CHARACTERISTICS (T_a=25℃)

Symbol	Characteristics	Min	Typ	Max	Unit	Test Conditions
BV_{CEO}	Collector-Emitter Breakdown Voltage	50			V	I_C=1mA, I_B=0
I_{CBO}	Collector Cut-off Current			0.1	μA	V_{CB}=60V, I_E=0
I_{EBO}	Emitter Cut-off Current			0.1	μA	V_{EB}=5V, I_C=0
H_{FE} (1)	DC Current Gain	50	185			V_{CE}=6V, I_C=0.1mA
H_{FE} (2)	DC Current Gain	110	200	600		V_{CE}=6V, I_C=1mA
$V_{CE(sat)}$	Collector- Emitter Saturation Voltage		0.15	0.3	V	I_C=100mA, I_B=10mA
$V_{BE(sat)}$	Base-Emitter Saturation Voltage		0.86	1	V	I_C=100mA, I_B=10mA
V_{BE}	Base-Emitter Voltage	0.55	0.62	0.65	V	V_{CE}=6V, I_C=1mA
fT	Current Gain-Bandwidth Product	150	250	450	MHz	V_{CE}=6V, I_C=10mA
Cob	Output Capacitance		3	4	pF	V_{CB}=6V, I_E=0，f=1MHz

h_{FE} Classification

R	J	H	F	E	K
110—180	135—220	170—270	200—320	250—400	300—600